Unit: mm

TOSHIBA Field Effect Transistor Silicon P Channel MOS Type (U-MOS IV)

# **TPCS8104**

Lithium Ion Battery Applications Notebook PC Applications Portable Equipment Applications

- Small footprint due to small and thin package
- Low drain-source ON resistance:  $RDS(ON) = 8.1 \text{ m}\Omega \text{ (typ.)}$
- High forward transfer admittance:  $|Y_{fs}| = 23 \text{ S (typ.)}$
- Low leakage current:  $IDSS = -10 \mu A (max) (VDS = -30 V)$
- Enhancement mode:  $V_{th}$  = -0.8 to -2.0 V ( $V_{DS}$  = -10 V,  $I_{D}$  = -1 mA)

### Absolute Maximum Ratings (Ta = 25°C)

Characteri	stics	Symbol	Rating	Unit
Drain-source voltage		$V_{DSS}$	-30	V
Drain-gate voltage (Ro	$GS = 20 \text{ k}\Omega$	$V_{DGR}$	-30	V
Gate-source voltage		V <sub>GSS</sub>	±20	V
Danie coment	DC (Note 1)	I <sub>D</sub>	-11	Α
Drain current	Pulse (Note 1)	I <sub>DP</sub>	-44	A
Drain power dissipatio	n (t = 10 s) (Note 2a)	P <sub>D</sub>	1.1	W
Drain power dissipatio	n (t = 10 s) (Note 2b)	P <sub>D</sub>	0.6	W
Single pulse avalanche	e energy (Note 3)	E <sub>AS</sub>	31.5	mJ
Avalanche current		I <sub>AR</sub>	-11	Α
Repetitive avalanche (N	energy lote 2a) (Note 4)	E <sub>AR</sub>	0.11	mJ
Channel temperature		T <sub>ch</sub>	150	°C
Storage temperature r	ange	T <sub>stg</sub>	-55 to 150	°C

(0.525)

1. DRAIN
2. 3. SOURCE
4. GATE

JEDEC

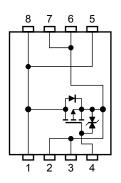
JEITA

TOSHIBA

2-3R1B

Weight: 0.035 g (typ.)

### **Circuit Configuration**



Note: (Note 1), (Note 2), (Note 3) and (Note 4): See the next page.

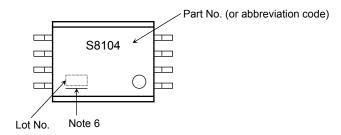
Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

This transistor is an electrostatic-sensitive device. Please handle with caution.

#### **Thermal Characteristics**

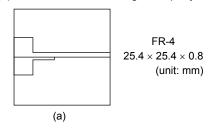
Characteristics	Symbol	Max	Unit
Thermal resistance, channel to ambient (t = 10 s) (Note 2a)	R <sub>th (ch-a)</sub>	114	°C/W
Thermal resistance, channel to ambient (t = 10 s) (Note 2b)	R <sub>th (ch-a)</sub>	208	°C/W

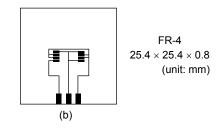
#### Marking (Note 5)



Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: (a) Device mounted on a glass-epoxy board (b) Device mounted on a glass-epoxy board (b)

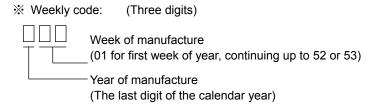




Note 3:  $V_{DD} = -24 \text{ V}$ ,  $T_{ch} = 25^{\circ}\text{C}$  (initial), L = 0.2 mH,  $R_G = 25 \Omega$ ,  $I_{AR} = -11 \text{ A}$ 

Note 4: Repetitive rating: pulse width limited by maximum channel temperature

Note 5: ○ on the lower left of the marking indicates Pin 1.



Note 6: A line under a Lot No. identifies the indication of product Labels.

Not underlined: [[Pb]]/INCLUDES > MCV

Underlined: [[G]]/RoHS COMPATIBLE or [[G]]/RoHS [[Pb]]

Please contact your TOSHIBA sales representative for details as to environmental matters such as the RoHS compatibility of Product. The RoHS is the Directive 2002/95/EC of the European Parliament and of the Council of 27 January 2003 on the restriction of the use of certain hazardous substances in electrical and electronic equipment.

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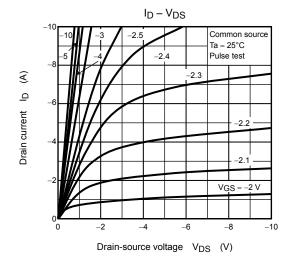
# **Electrical Characteristics (Ta = 25°C)**

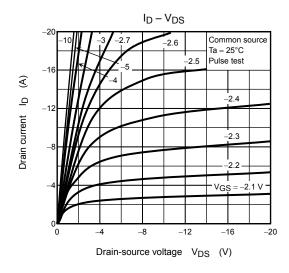
Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current		I <sub>GSS</sub>	$V_{GS} = \pm 16 \text{ V}, V_{DS} = 0 \text{ V}$	_	_	±10	μА
Drain cut-OFF current		I <sub>DSS</sub>	$V_{DS} = -30 \text{ V}, V_{GS} = 0 \text{ V}$	_	_	-10	μА
Drain-source breakdown voltage		V <sub>(BR) DSS</sub>	$I_D = -10 \text{ mA}, V_{GS} = 0 \text{ V}$	-30	_	_	٧
Dialii-Source breakdov	vii voitage	V <sub>(BR)DSX</sub>	$I_D = -10 \text{ mA}, V_{GS} = 20 \text{ V}$			_	
Gate threshold voltage		V <sub>th</sub>	$V_{DS} = -10 \text{ V}, I_D = -1 \text{ mA}$	-0.8	_	-2.0	V
Drain-source ON resistance		D	$V_{GS} = -4 \text{ V}, I_D = -5.5 \text{ A}$	_	12	18	- mΩ
		R <sub>DS</sub> (ON)	$V_{GS} = -10 \text{ V}, I_D = -5.5 \text{ A}$	_	8.1	12	
Forward transfer admittance		Y <sub>fs</sub>	$V_{DS} = -10 \text{ V}, I_D = -5.5 \text{ A}$	11	23		S
Input capacitance		C <sub>iss</sub>	V <sub>DS</sub> = -10 V, V <sub>GS</sub> = 0 V, f = 1 MHz	_	5710	_	pF
Reverse transfer capacitance		C <sub>rss</sub>		_	560	_	
Output capacitance		Coss		_	590	_	
Switching time	Rise time	t <sub>r</sub>	V <sub>GS</sub> <sub>-10</sub> V	_	18		- ns
	Turn-ON time	t <sub>on</sub>		_	23	_	
	Fall time	t <sub>f</sub>	Ľ.	_	109	l	
	Turn-OFF time	t <sub>off</sub>	$V_{DD} \simeq -15 \text{ V}$ Duty $\leq 1\%$ , $t_W = 10 \mu\text{s}$	_	396		
Total gate charge (gate-source plus gate-drain)		Qg	V <sub>DD</sub> ≈ -24 V, V <sub>GS</sub> = 10 V,	_	107	_	nC
Gate-source charge 1		Q <sub>gs1</sub>	$I_D = -11 \text{ A}$	_	12	_	
Gate-drain ("miller") charge		Q <sub>gd</sub>		_	20	_	

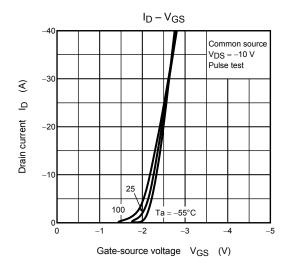
## **Source-Drain Ratings and Characteristics (Ta = 25°C)**

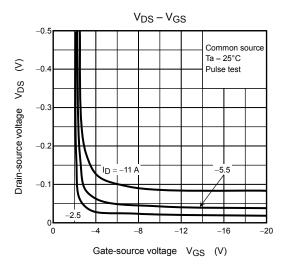
Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit	
Drain reverse current	Pulse	(Note 1)	I <sub>DRP</sub>	_	_	_	-44	Α
Forward voltage (diode)			V <sub>DSF</sub>	I <sub>DR</sub> = -11 A, V <sub>GS</sub> = 0 V	_	_	1.2	V

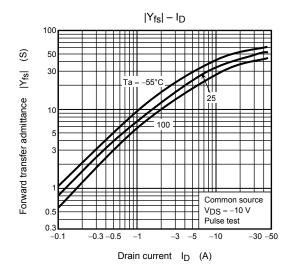
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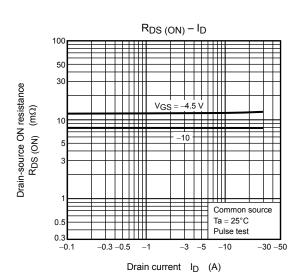


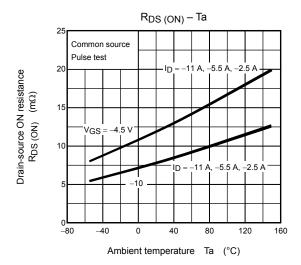


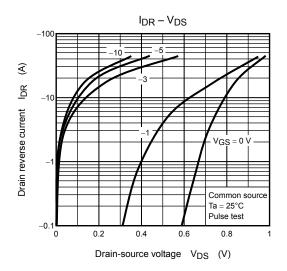


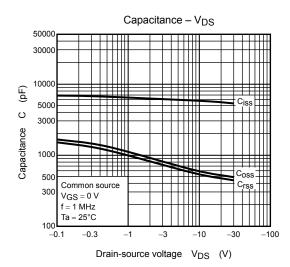


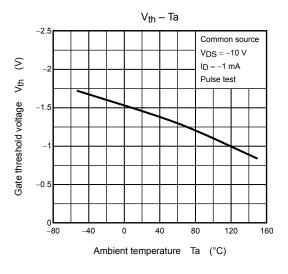


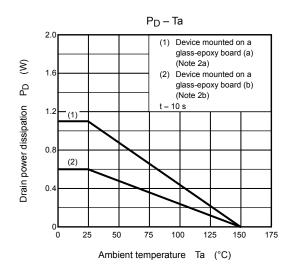


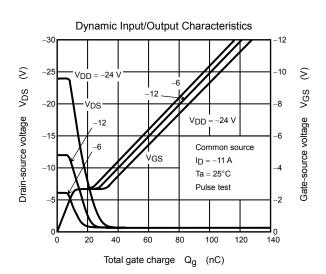


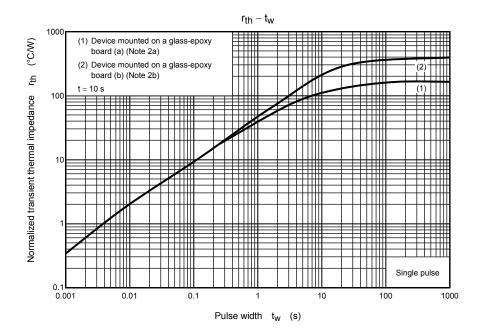


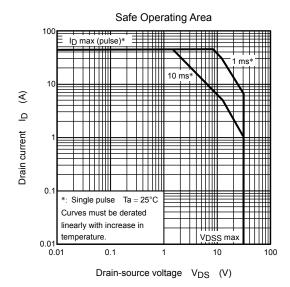












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